

Supporting Information

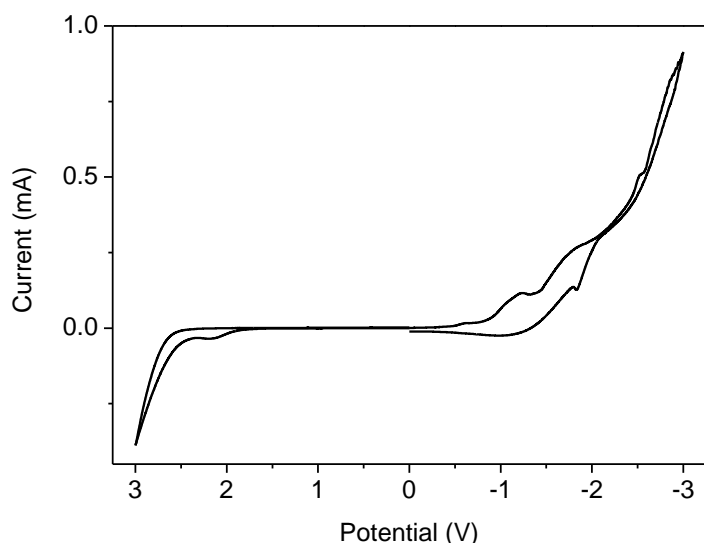
N-doping of thermally polymerizable fullerenes as an Electron Transporting Layer for Inverted Polymer Solar Cells

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10 Figure S1. Cyclic voltammograms of P-PCBM-S films on ITO glass in a 0.1 M solution of TBAPF₆ in acetonitrile scanned at a rate of 100 mV/s.

Table S1. Electronic structure parameters of P-PCBM-S film

material	Ionization potential ^a (eV)	Electron affinity ^b (eV)	E_g^{el} (eV) ^c	E_g^{opt} (eV) ^d
P-PCBM-S	5.96 (5.81) ^e	3.67	2.29	2.14

15 ^a Determined from the onset oxidation potential. ^b Determined from the onset reduction potential. ^c Electrochemical bandgap $E_g^{\text{el}} = \text{ionization potential} - \text{electron affinity}$. ^d Optical bandgap E_g^{opt} estimated from the optical absorption-onset of P-PCBM-S thin films. ^e Determined from $\text{ionization potential} = \text{electron affinity} + E_g^{\text{opt}}$.